



Si7866ADP vs. Si7866DP

Description: N-Channel, 20 V (D-S) MOSFET

Package: PowerPAK® SO-8

Pin Out: Identical

Part Number Replacements:

Si7866ADP-T1-E3 Replaces Si7866DP-T1-E3

Si7866ADP-T1-E3 Replaces Si7866DP-T1

ABSOLUTE MAXIMUM RATINGS $T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted					
Parameter	Symbol	Si7866ADP	Si7866DP	Unit	
Drain-Source Voltage	V_{DS}	20	20	V	
Gate-Source Voltage	V_{GS}	± 20	± 20		
Continuous Drain Current	$T_A = 25\text{ }^\circ\text{C}$	I_D	35	29	A
	$T_A = 70\text{ }^\circ\text{C}$		28	25	
Pulsed Drain Current	I_{DM}	70	60		
Continuous Source Current (MOSFET Diode Conduction)	I_S	4.9	4.5		
Power Dissipation	$T_A = 25\text{ }^\circ\text{C}$	P_D	5.4	5.4	W
	$T_A = 70\text{ }^\circ\text{C}$		3.4	3.4	
Operating Junction and Storage Temperature Range	T_J and T_{stg}	- 55 to 150	- 55 to 150	$^\circ\text{C}$	
Maximum Junction-to-Ambient	R_{thJA}	23	23	$^\circ\text{C/W}$	

SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted								
Parameter	Symbol	Si7866ADP			Si7866DP			Unit
		Min	Typ	Max	Min	Typ	Max	
Static								
Gate-Threshold Voltage	$V_{GS(th)}$	0.8		2.2	0.8		2.1	V
Gate-Body Leakage	I_{GSS}			± 100			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}			1			1	μA
On-State Drain Current	$V_{GS} = 10\text{ V}$ $I_{D(on)}$	30			30			A
Drain-Source On-Resistance	$V_{GS} = 10\text{ V}$ $r_{DS(on)}$		0.0019	0.0024		0.0020	0.0025	Ω
	$V_{GS} = 4.5\text{ V}$		0.0023	0.0030		0.0026	0.00375	
Forward Transconductance	g_{fs}		110			95		S
Diode Forward Voltage	V_{SD}		0.65	1.1		0.68	1.1	V
Dynamic								
Total Gate Charge	Q_g		39	60		40	60	nC
Gate-Source Charge	Q_{gs}		12.5			15		
Gate-Drain Charge	Q_{gd}		10.3			11		
Gate Resistance	R_g	0.5	1.1	1.7	0.5	1.2	1.8	Ω
Switching								
Turn-On Time ^a	$t_{d(on)}$		34	50		70	100	ns
	t_r		120	180		60	90	
Turn-Off Time ^a	$t_{d(off)}$		42	65		105	160	
	t_f		12	20		55	85	
Source-Drain Reverse Recovery Time	t_{rr}		51	75		65	100	

Notes:

a. Datasheet test conditions differ; $R_L = 1\ \Omega$, $I_D = 10\text{ A}$, $R_g = 1\ \Omega$ on the Si7866ADP and $R_L = 10\ \Omega$, $I_D = 1\text{ A}$, $R_g = 6\ \Omega$ on the Si7866DP.

Specification comparisons are supplied as a courtesy to compare two devices and do not constitute a commercial product datasheet or any guarantee of identical performance. Designers should refer to the appropriate datasheets of the same number for guaranteed specification limits.